

### FAST RECOVERY DIODES

### Hockey Puk Version

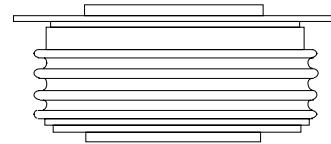
#### Features

- High power FAST recovery diode series
- 2.0 to 3.0  $\mu$ s recovery time
- High voltage ratings up to 2500V
- High current capability
- Optimized turn on and turn off characteristics
- Low forward recovery
- Fast and soft reverse recovery
- Press-puk encapsulation
- Case style conform to JEDEC DO-200AB (B-PUK)
- Maximum junction temperature 150°C
- RoHS Compliant

#### Typical Applications

- Snubber diode for GTO
- High voltage free-wheeling diode
- Fast recovery rectifier applications

700A  
790A



case style DO-200AB (B-PUK)

#### Major Ratings and Characteristics

Parameters	SD703C..L		Units
	S20	S30	
$I_{F(AV)}$	700	790	A
@ $T_{hs}$	55	55	°C
$I_{F(RMS)}$	1320	1470	A
$I_{FSM}$ @ 50Hz	9300	9600	A
@ 60Hz	9730	10050	A
$V_{RRM}$ range	1200 to 2500	1200 to 2500	V
$t_{rr}$	2.0	3.0	$\mu$ s
@ $T_j$	25	25	°C
$T_j$	- 40 to 150		°C

**ELECTRICAL SPECIFICATIONS**

**Voltage Ratings**

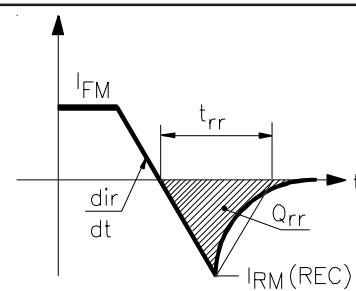
Type number	Voltage Code	$V_{RRM}$ , maximum repetitive peak reverse voltage V	$V_{RSM}$ , maximum non-repetitive peak rev. voltage V	$I_{RRM}$ max. @ $T_J = T_J$ max. mA
SD703C..L	12	1200	1300	50
	16	1600	1700	
	20	2000	2100	
	25	2500	2600	

**Forward Conduction**

Parameter	SD703C..L		Units	Conditions
	S20	S30		
$I_{F(AV)}$ Max. average forward current @ case temperature	700 (365)	790 (400)	A	180° conduction, half sine wave
	55 (85)	55 (85)	°C	Double side (single side) cooled
$I_{F(RMS)}$ Max. RMS forward current	1320	1470	A	@ 25°C heatsink temperature double side cooled
$I_{FSM}$ Max. peak, one-cycle forward, non-repetitive surge current	9300	9600	A	t = 10ms No voltage reappplied
	9730	10050		t = 8.3ms
	7820	8070		t = 10ms 100% $V_{RRM}$
	8190	8450		t = 8.3ms reappplied
$I^2t$ Maximum $I^2t$ for fusing	432	460	KA <sup>2</sup> s	t = 10ms No voltage reappplied
	395	420		t = 8.3ms
	306	326		t = 10ms 100% $V_{RRM}$
	279	297		t = 8.3ms reappplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	4320	4600	KA <sup>2</sup> √s	t = 0.1 to 10ms, no voltage reappplied
$V_{F(TO)1}$ Low level value of threshold voltage	1.00	0.95	V	$(16.7\% \times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)})$ , $T_J = T_J$ max.
$V_{F(TO)2}$ High level value of threshold voltage	1.11	1.05		$(I > \pi \times I_{F(AV)})$ , $T_J = T_J$ max.
$r_{f1}$ Low level value of forward slope resistance	0.80	0.60	mΩ	$(16.7\% \times \pi \times I_{F(AV)} < I < \pi \times I_{F(AV)})$ , $T_J = T_J$ max.
$r_{f2}$ High level value of forward slope resistance	0.76	0.56		$(I > \pi \times I_{F(AV)})$ , $T_J = T_J$ max.
$V_{FM}$ Max. forward voltage drop	2.20	1.85	V	$I_{pk} = 1500A$ , $T_J = T_J$ max, $t_p = 10ms$ sinusoidal wave

**Recovery Characteristics**

Code	$T_J = 25^\circ C$ typical $t_{rr}$ @ 25% $I_{RRM}$ (μs)	Test conditions			Max. values @ $T_J = 150^\circ C$		
		$I_{pk}$ Square Pulse (A)	di/dt (A/μs)	$V_r$ (V)	$t_{rr}$ @ 25% $I_{RRM}$ (μs)	$Q_{rr}$ (μC)	$I_{rr}$ (A)
S20	2.0	1000	50	-50	3.5	240	110
S30	3.0	1000	50	-50	5.0	380	130



Thermal and Mechanical Specifications

Parameter	SD703C..L		Units	Conditions
	S20	S30		
T <sub>J</sub> Max. junction operating temperature range	-40 to 150		°C	
T <sub>stg</sub> Max. storage temperature range	-40 to 150			
R <sub>thJ-hs</sub> Max. thermal resistance, case junction to heatsink	0.092 0.046		K/W	DCoperation single side cooled DCoperation double side cooled
F Mounting force, ±10%	9800 (1000)		N (Kg)	
wt Approximate weight	250		g	
Case style	DO-200AB (B-PUK)			See Outline Table

$\Delta R_{thJ-hs}$  Conduction

(The following table shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.011	0.011	0.008	0.008	K/W	T <sub>J</sub> = T <sub>J</sub> max.
120°	0.013	0.014	0.013	0.013		
90°	0.017	0.017	0.018	0.018		
60°	0.024	0.025	0.026	0.026		
30°	0.043	0.043	0.043	0.044		

Ordering Information Table

**Device Code**

<b>SD</b>	<b>70</b>	<b>3</b>	<b>C</b>	<b>25</b>	<b>S20</b>	<b>L</b>
①	②	③	④	⑤	⑥	⑦

- 1** - Diode
- 2** - Essential part number
- 3** - 3 = Fast recovery
- 4** - C = Ceramic Puk
- 5** - Voltage code: Code x 100 = V<sub>RRM</sub> (See Voltage Ratings table)
- 6** - t<sub>rr</sub> code
- 7** - L = Puk Case DO-200AB (B-PUK)

Outline Table

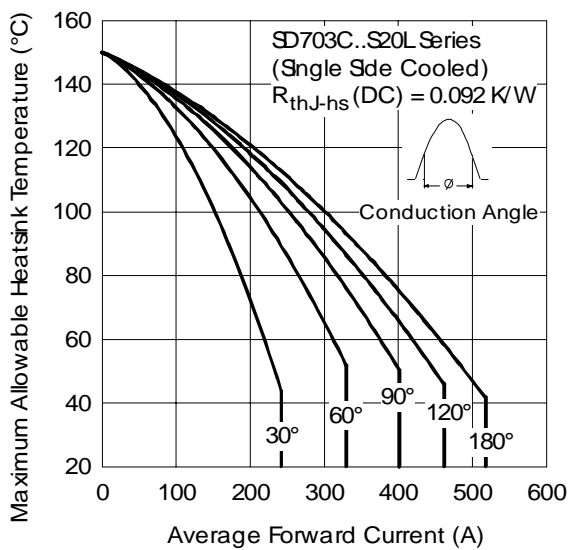
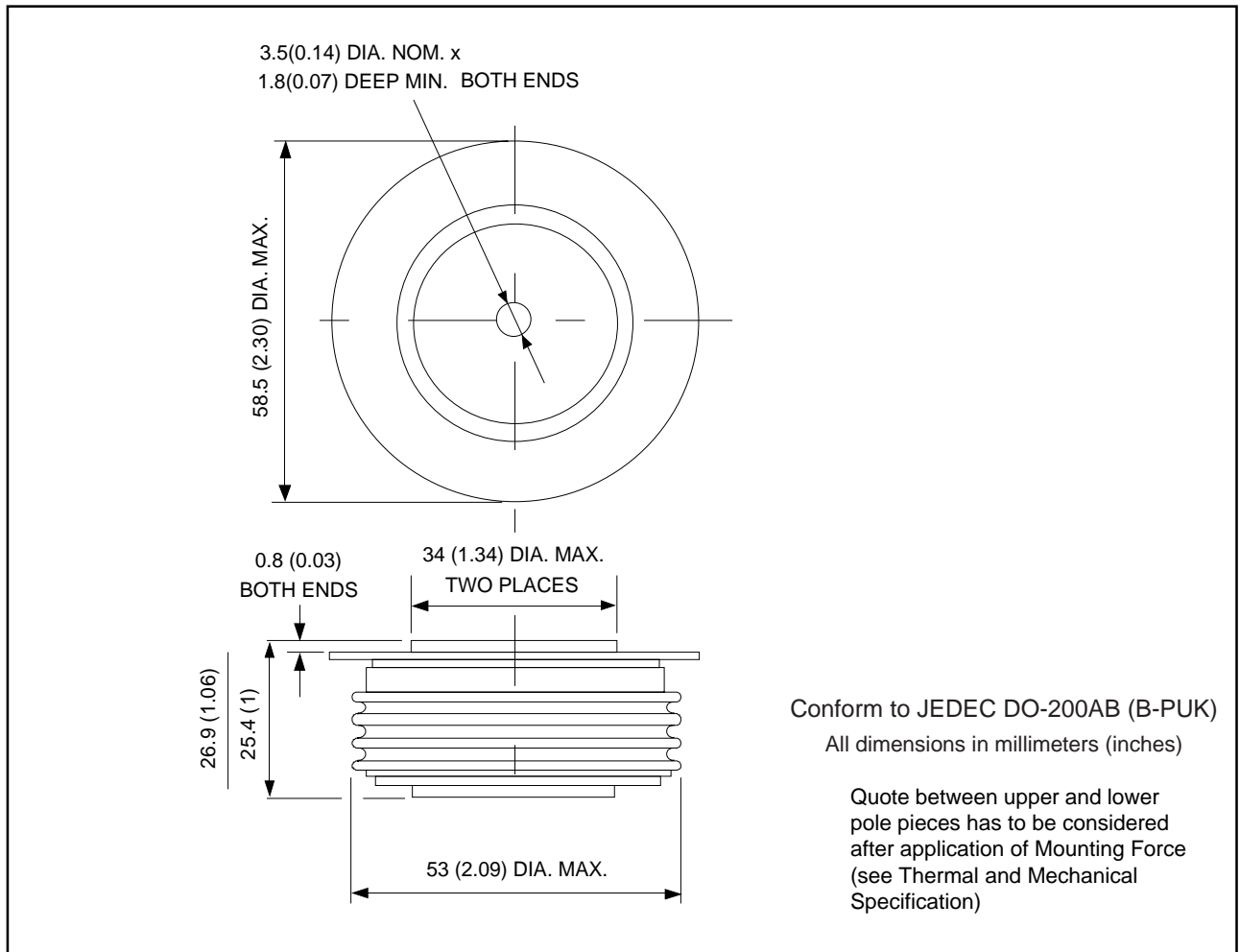


Fig. 1 - Current Ratings Characteristics

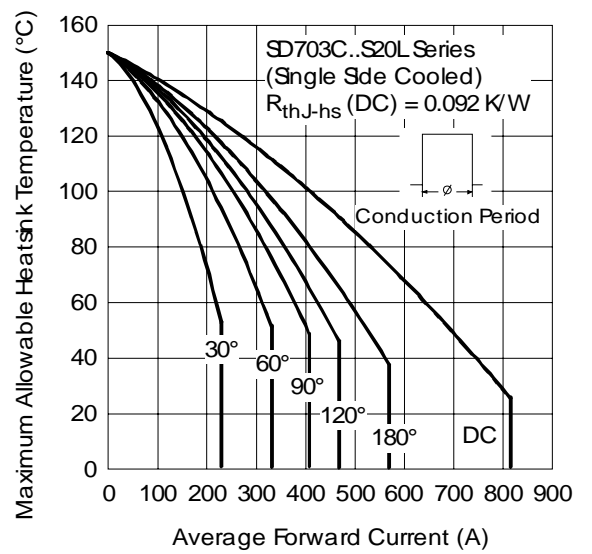


Fig. 2 - Current Ratings Characteristics

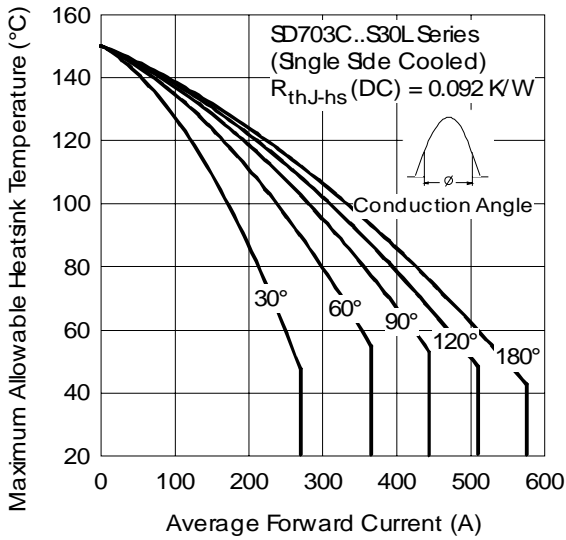


Fig. 3 - Current Ratings Characteristics

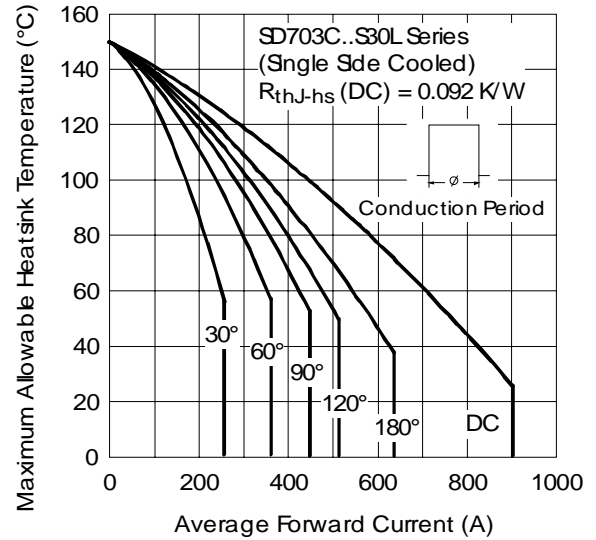


Fig. 4 - Current Ratings Characteristics

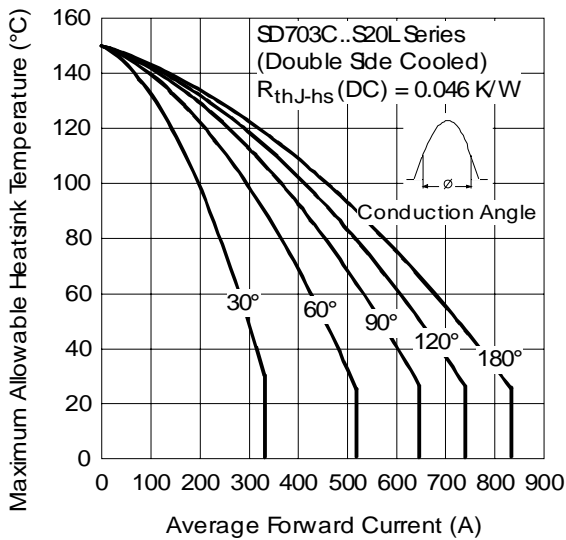


Fig. 5 - Current Ratings Characteristics

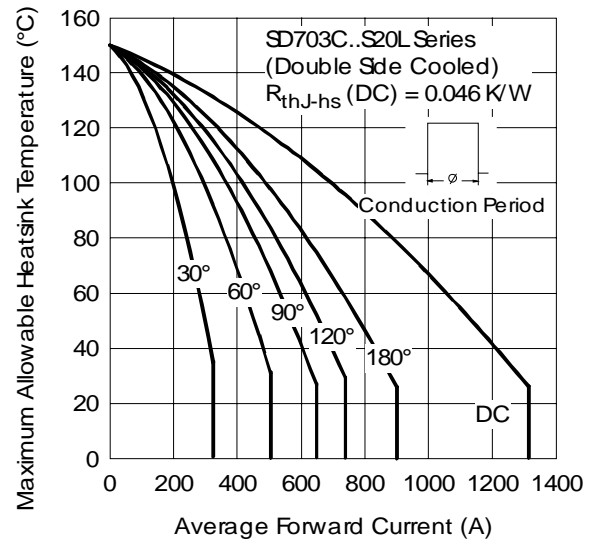


Fig. 6 - Current Ratings Characteristics

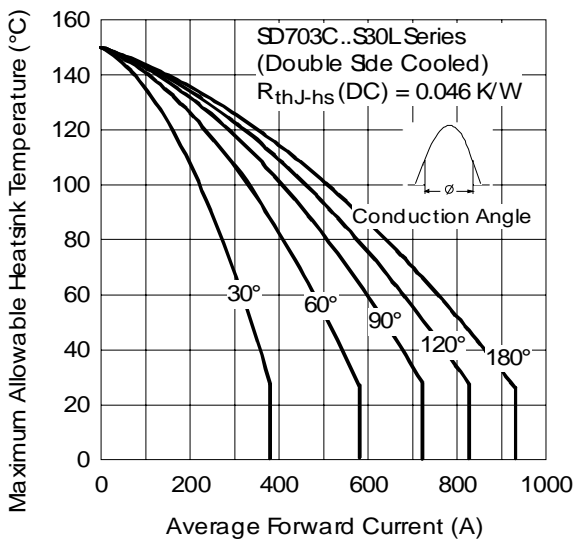


Fig. 7 - Current Ratings Characteristics

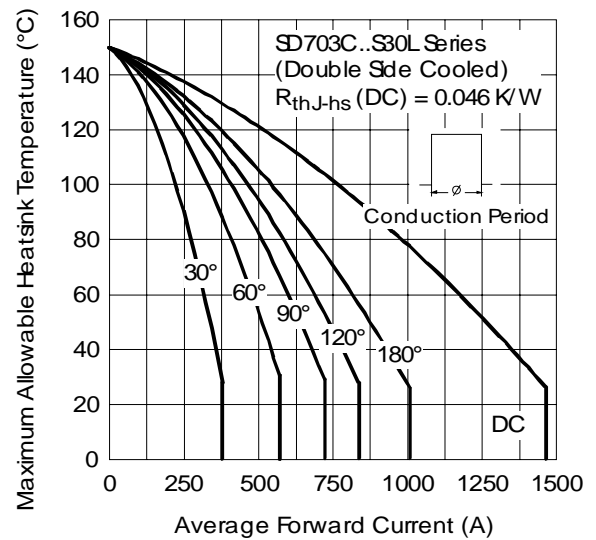


Fig. 8 - Current Ratings Characteristics

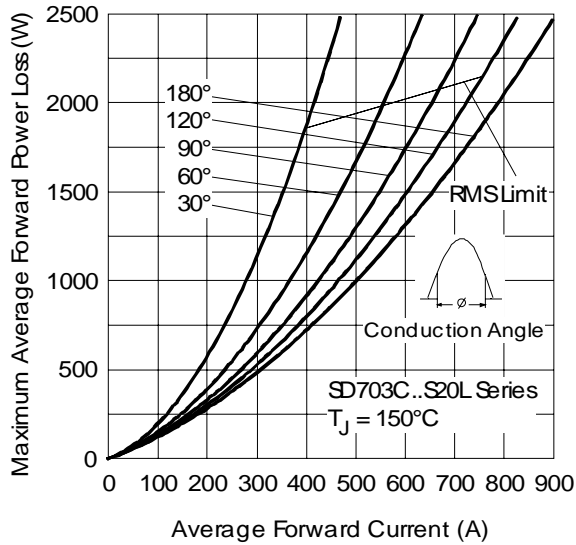


Fig. 9 - Forward Power Loss Characteristics

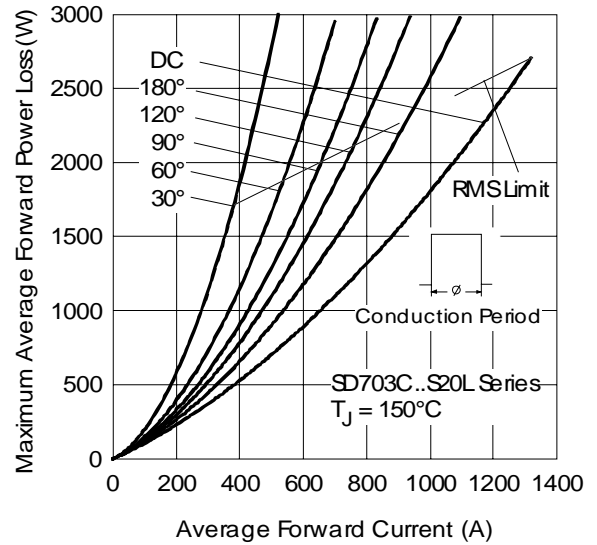


Fig. 10 - Forward Power Loss Characteristics

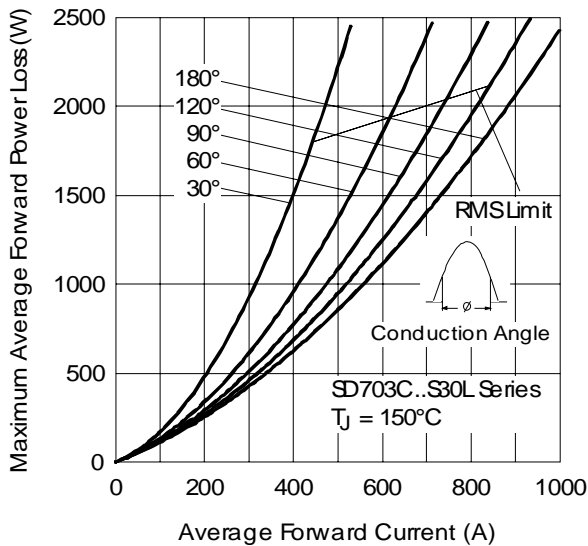


Fig. 11 - Forward Power Loss Characteristics

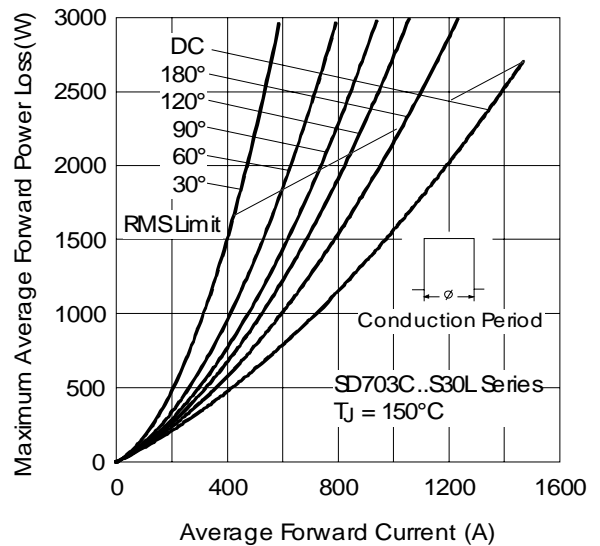


Fig. 12 - Forward Power Loss Characteristics

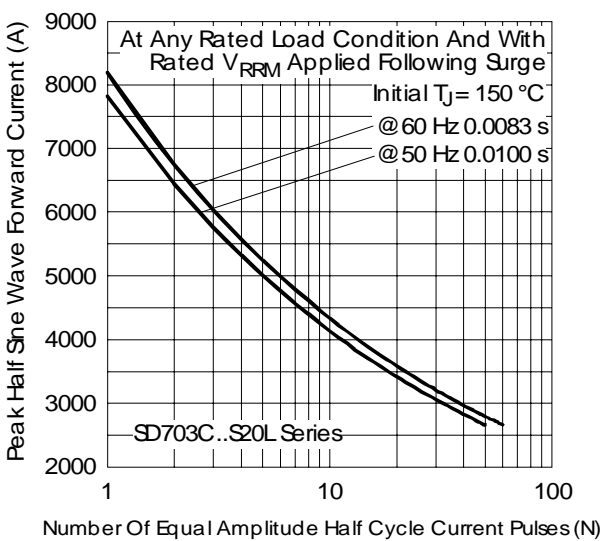


Fig. 13 - Maximum Non-repetitive Surge Current Single and Double Side Cooled

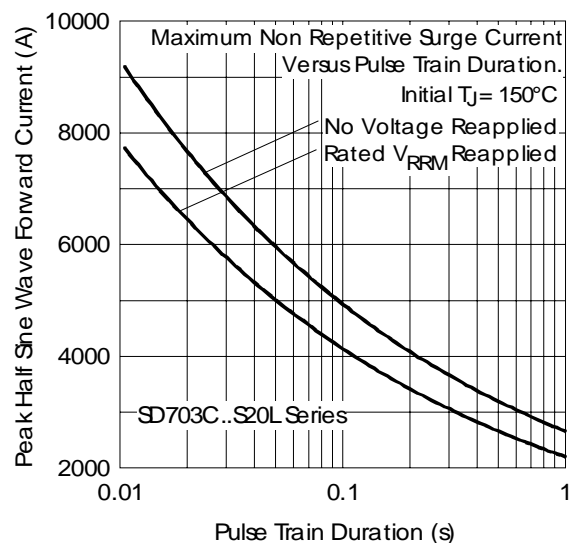


Fig. 14 - Maximum Non-repetitive Surge Current Single and Double Side Cooled

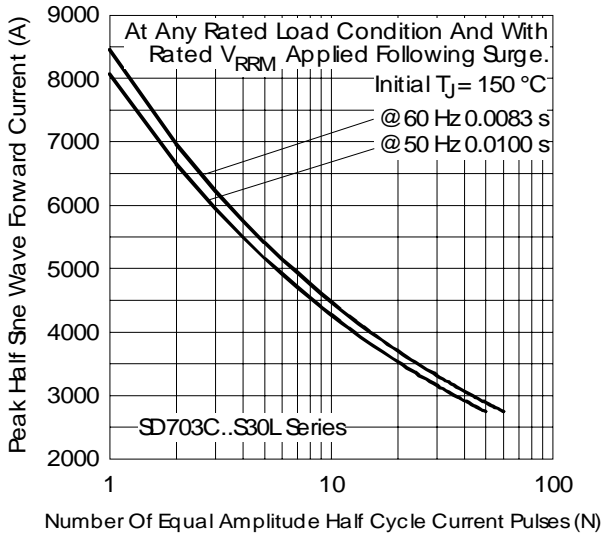


Fig. 15 - Maximum Non-repetitive Surge Current Single and Double Side Cooled

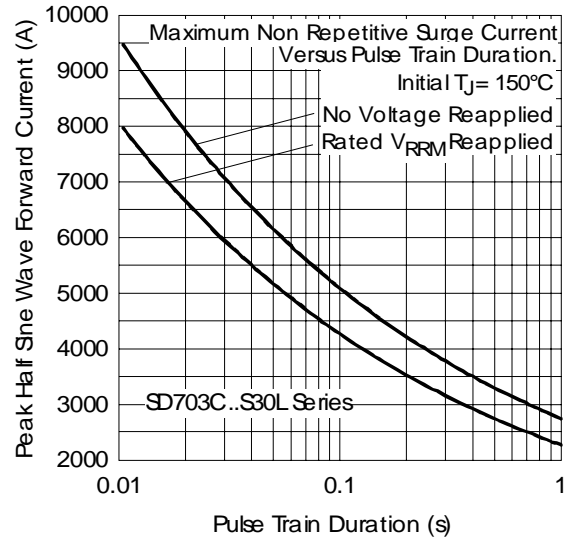


Fig. 16 - Maximum Non-repetitive Surge Current Single and Double Side Cooled

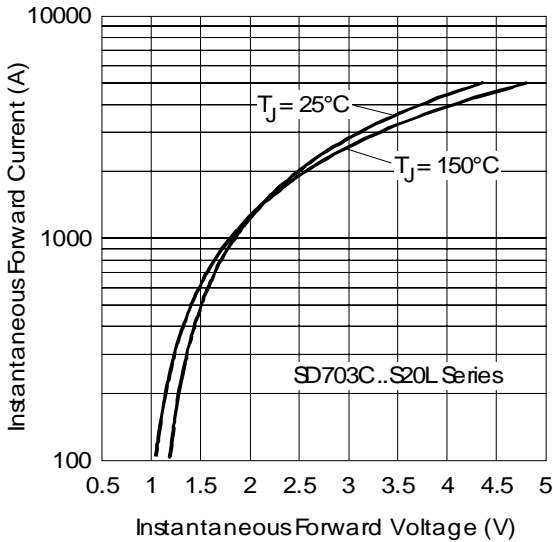


Fig. 17 - Forward Voltage Drop Characteristics

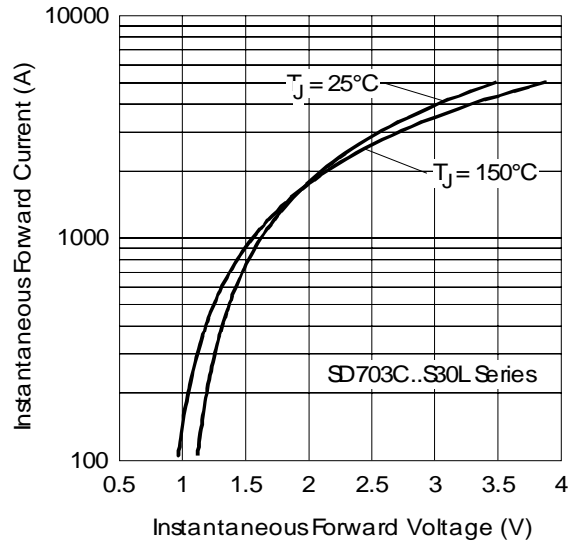


Fig. 18 - Forward Voltage Drop Characteristics

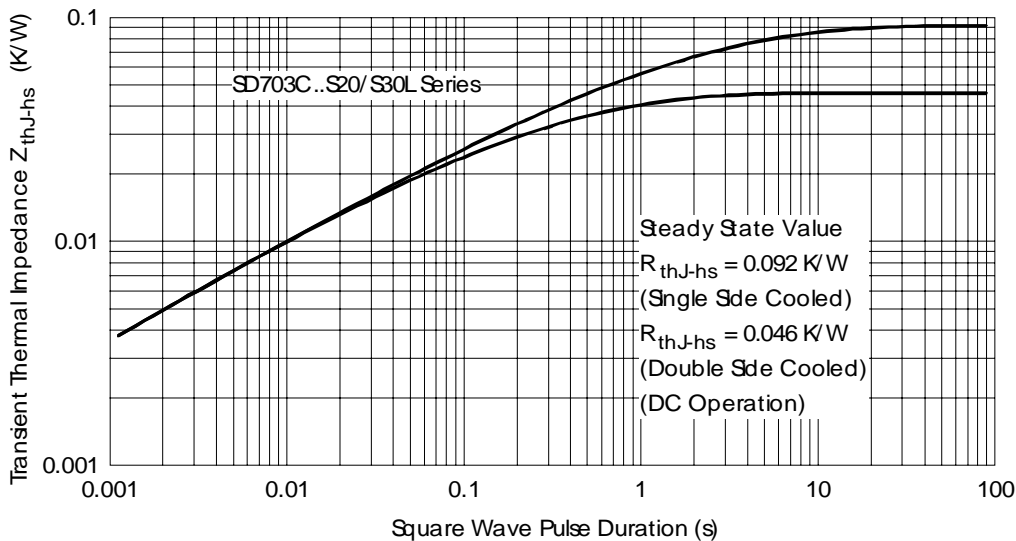


Fig. 19 - Thermal Impedance  $Z_{thJ-hs}$  Characteristic

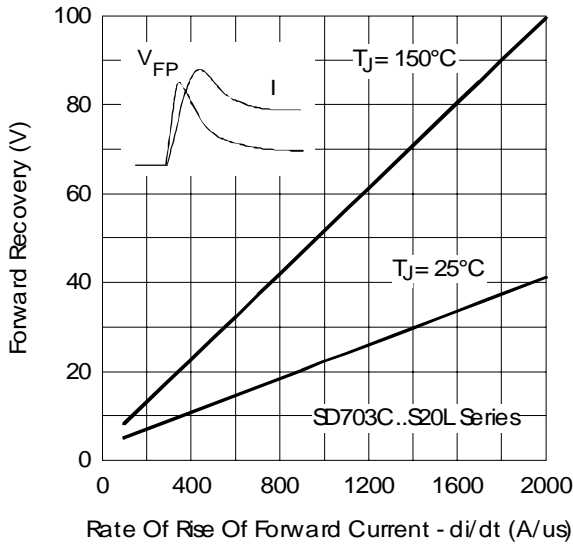


Fig. 20 - Typical Forward Recovery Characteristics

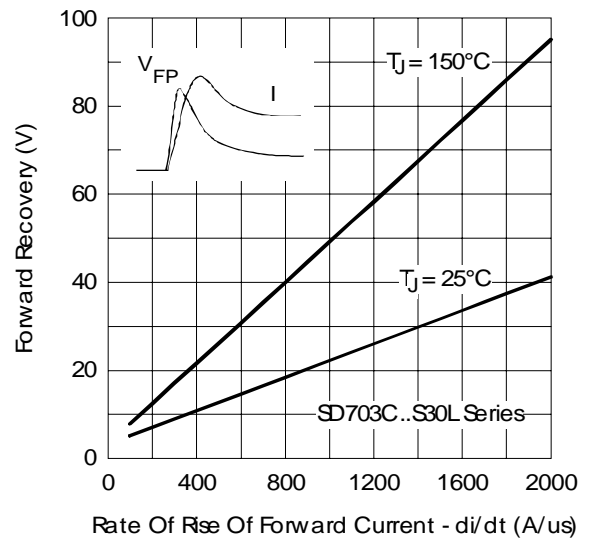


Fig. 21 - Typical Forward Recovery Characteristics

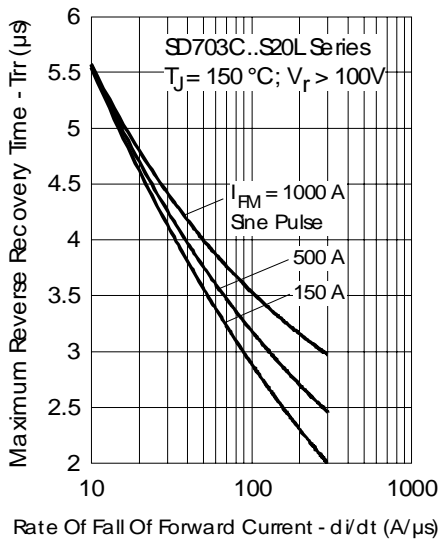


Fig. 22 - Recovery Time Characteristics

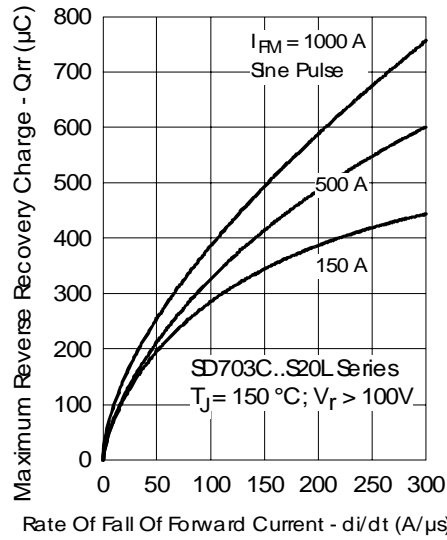


Fig. 23 - Recovery Charge Characteristics

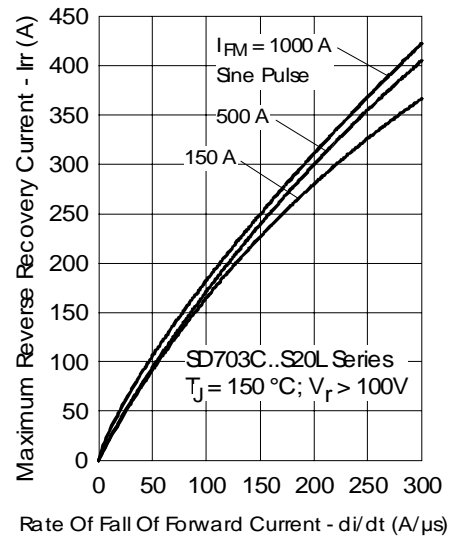


Fig. 24 - Recovery Current Characteristics

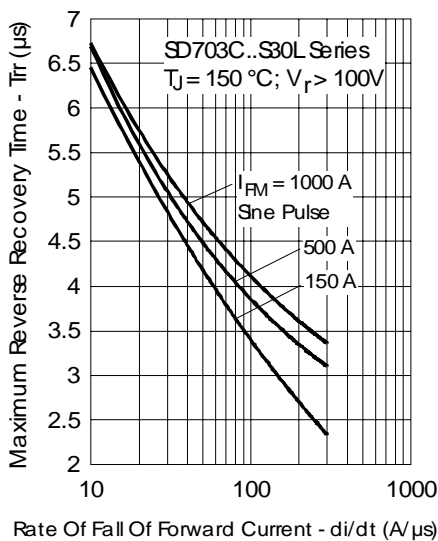


Fig. 25 - Recovery Time Characteristics

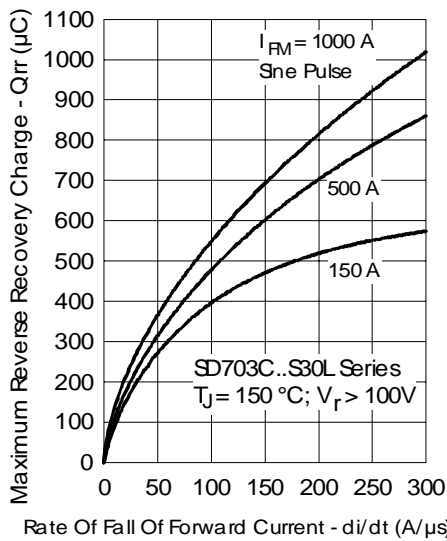


Fig. 26 - Recovery Charge Characteristics

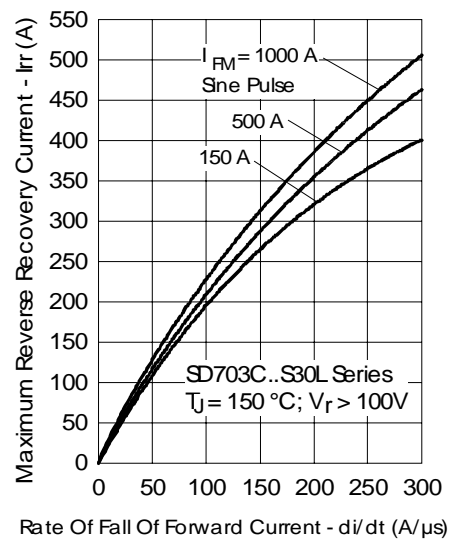


Fig. 27 - Recovery Current Characteristics



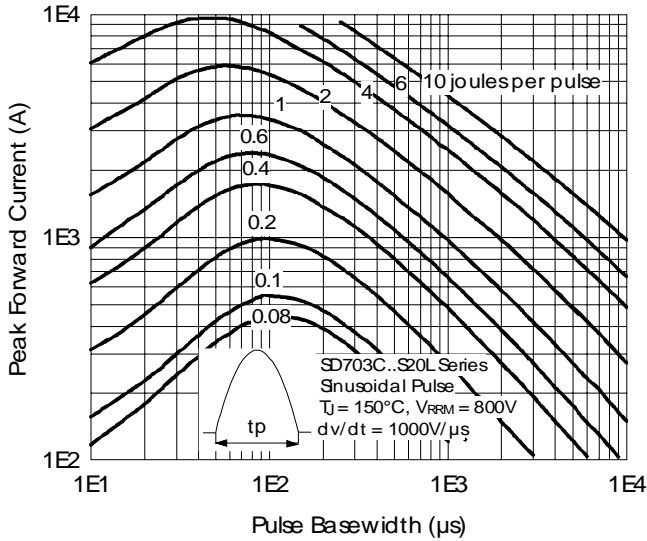


Fig. 28 - Maximum Total Energy Loss Per Pulse Characteristics

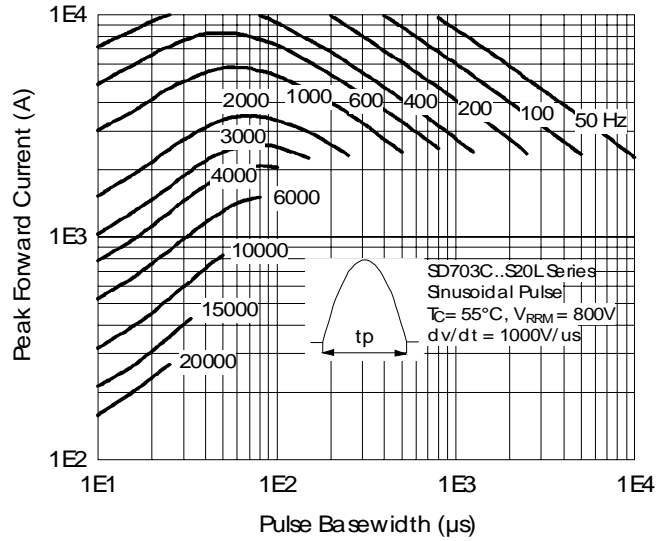


Fig. 29 - Frequency Characteristics

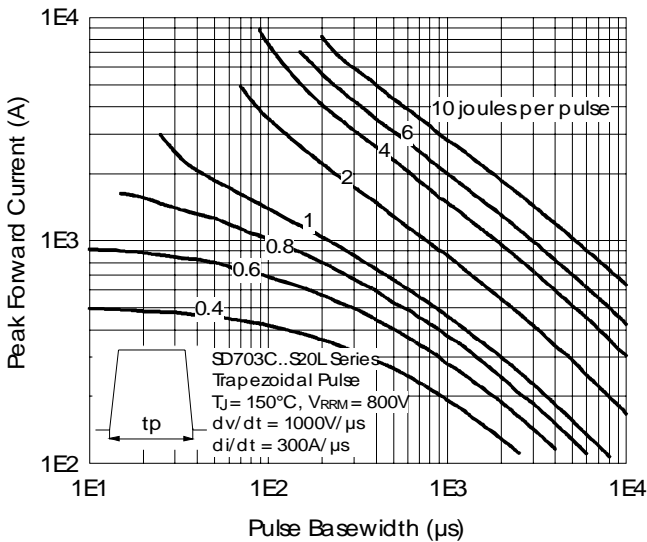


Fig. 30 - Maximum Total Energy Loss Per Pulse Characteristics

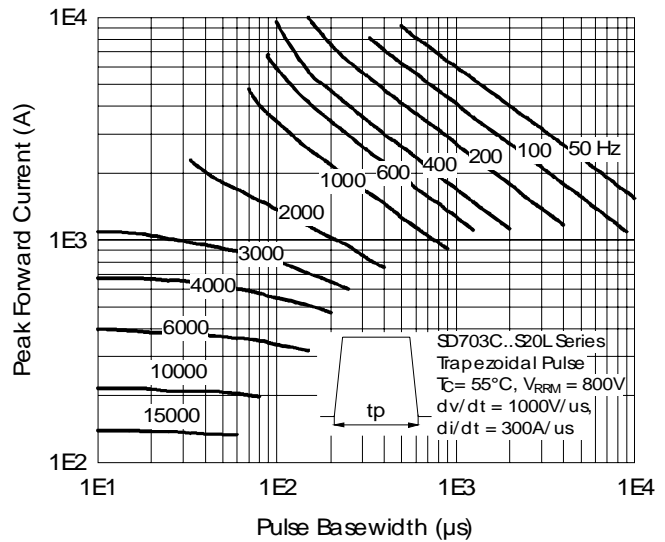


Fig. 31 - Frequency Characteristics

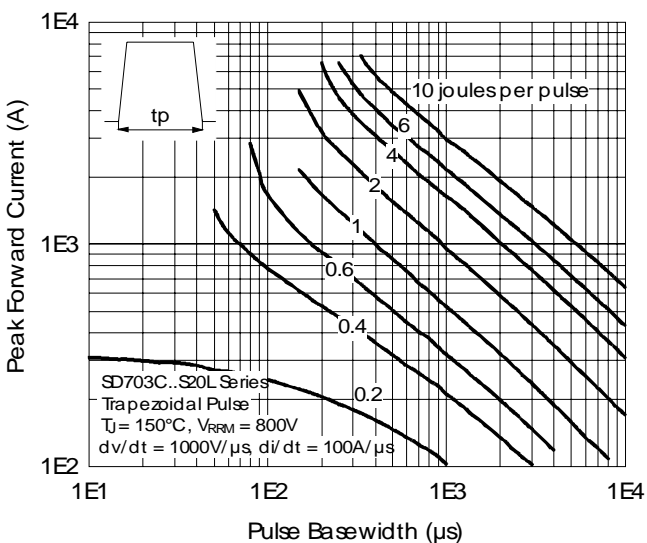


Fig. 32 - Maximum Total Energy Loss Per Pulse Characteristics

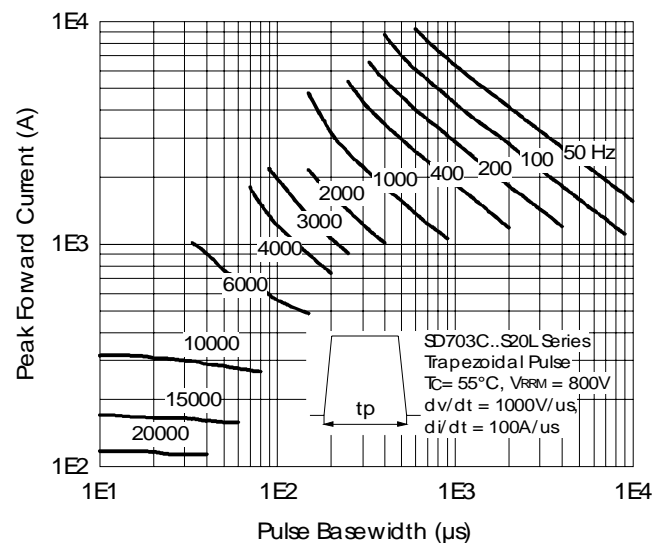


Fig. 33 - Frequency Characteristics

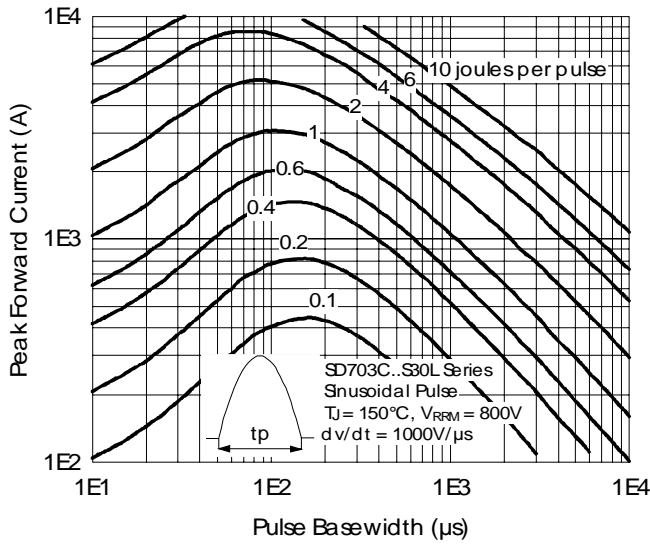


Fig. 34 - Maximum Total Energy Loss Per Pulse Characteristics

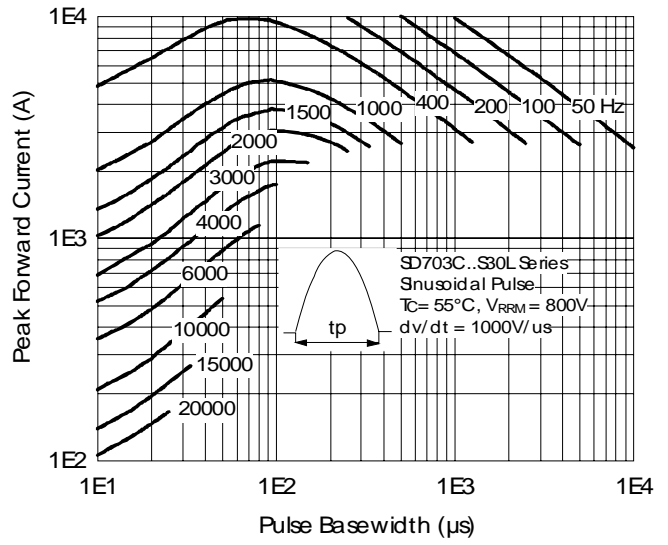


Fig. 35 - Frequency Characteristics

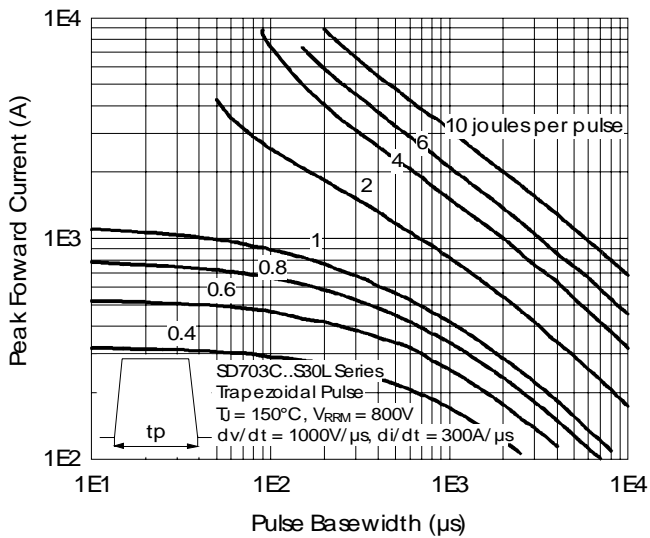


Fig. 36 - Maximum Total Energy Loss Per Pulse Characteristics

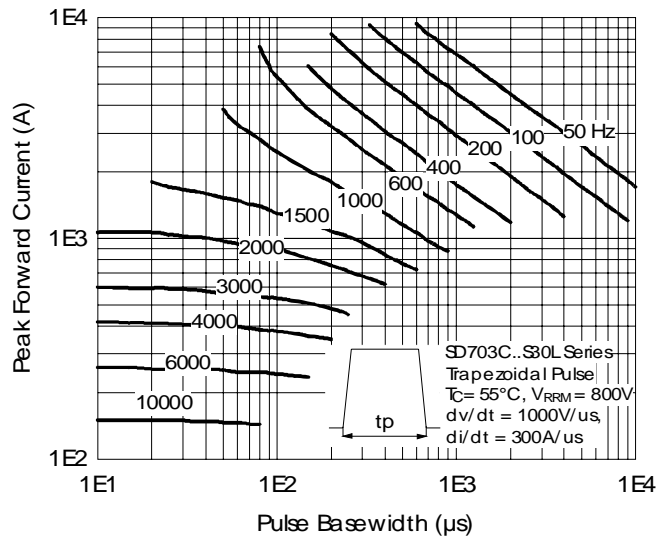


Fig. 37 - Frequency Characteristics

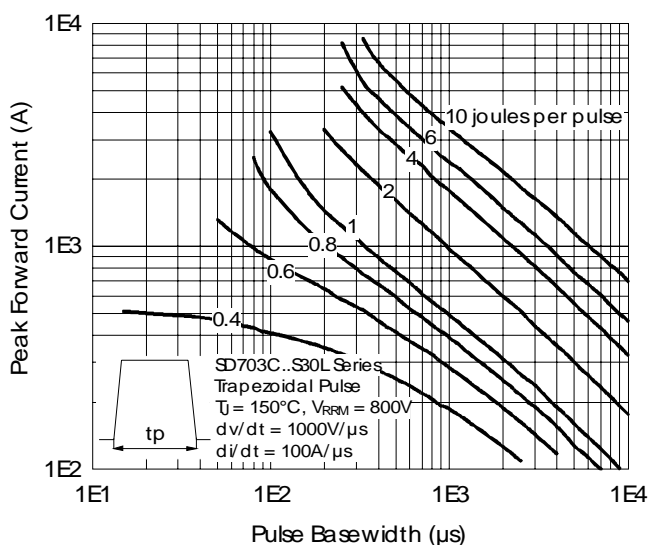


Fig. 38 - Maximum Total Energy Loss Per Pulse Characteristics

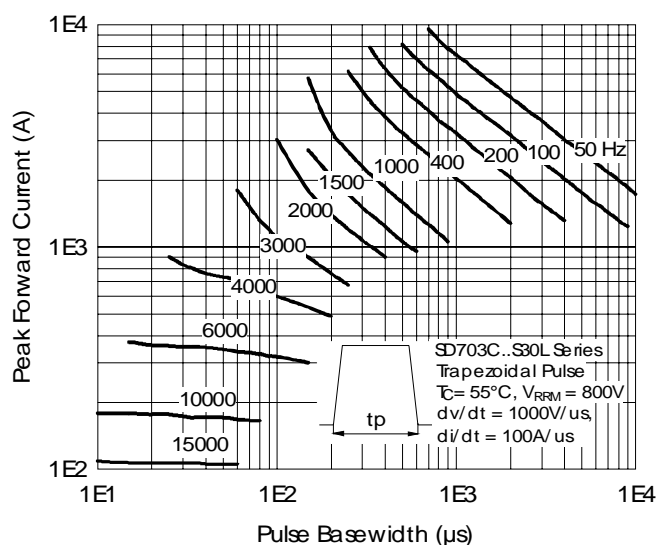


Fig. 39 - Frequency Characteristics

Data and specifications subject to change without notice.  
This product has been designed and qualified for Industrial Level.  
Qualification Standards can be found on IR's Web site.

International  
**IOR** Rectifier

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